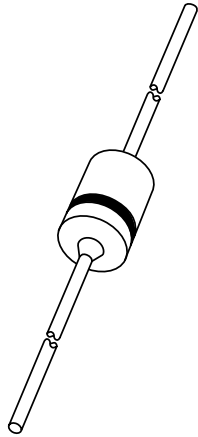


DATA SHEET



1N4148; 1N4448 High-speed diodes

Product specification

High-speed diodes

1N4148; 1N4448

FEATURES

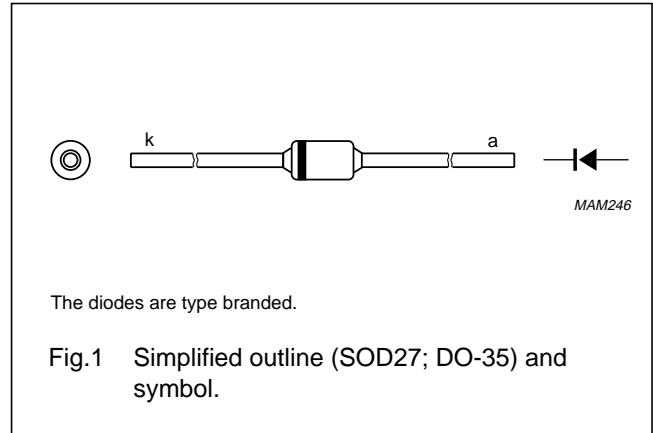
- Hermetically sealed leaded glass SOD27 (DO-35) package
- High switching speed: max. 4 ns
- General application
- Continuous reverse voltage: max. 100 V
- Repetitive peak reverse voltage: max. 100 V
- Repetitive peak forward current: max. 450 mA.

APPLICATIONS

- High-speed switching.

DESCRIPTION

The 1N4148 and 1N4448 are high-speed switching diodes fabricated in planar technology, and encapsulated in hermetically sealed leaded glass SOD27 (DO-35) packages.



MARKING

TYPE NUMBER	MARKING CODE
1N4148	1N4148PH or 4148PH
1N4448	1N4448

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
1N4148	-	hermetically sealed glass package; axial leaded; 2 leads	SOD27
1N4448			

High-speed diodes

1N4148; 1N4448

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	repetitive peak reverse voltage		–	100	V
V_R	continuous reverse voltage		–	100	V
I_F	continuous forward current	see Fig.2; note 1	–	200	mA
I_{FRM}	repetitive peak forward current		–	450	mA
I_{FSM}	non-repetitive peak forward current	square wave; $T_j = 25\text{ °C}$ prior to surge; see Fig.4 $t = 1\ \mu\text{s}$ $t = 1\ \text{ms}$ $t = 1\ \text{s}$	– – –	4 1 0.5	A A A
P_{tot}	total power dissipation	$T_{amb} = 25\text{ °C}$; note 1	–	500	mW
T_{stg}	storage temperature		–65	+200	°C
T_j	junction temperature		–	200	°C

Note

1. Device mounted on an FR4 printed-circuit board; lead length 10 mm.

ELECTRICAL CHARACTERISTICS $T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_F	forward voltage 1N4148 1N4448	see Fig.3 $I_F = 10\ \text{mA}$ $I_F = 5\ \text{mA}$ $I_F = 100\ \text{mA}$	– 0.62 –	1 0.72 1	V V V
I_R	reverse current	$V_R = 20\ \text{V}$; see Fig.5 $V_R = 20\ \text{V}$; $T_j = 150\text{ °C}$; see Fig.5	–	25 50	nA μA
I_{R1}	reverse current; 1N4448	$V_R = 20\ \text{V}$; $T_j = 100\text{ °C}$; see Fig.5	–	3	μA
C_d	diode capacitance	$f = 1\ \text{MHz}$; $V_R = 0\ \text{V}$; see Fig.6	–	4	pF
t_{rr}	reverse recovery time	when switched from $I_F = 10\ \text{mA}$ to $I_R = 60\ \text{mA}$; $R_L = 100\ \Omega$; measured at $I_R = 1\ \text{mA}$; see Fig.7	–	4	ns
V_{fr}	forward recovery voltage	when switched from $I_F = 50\ \text{mA}$; $t_r = 20\ \text{ns}$; see Fig.8	–	2.5	V

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-tp)}$	thermal resistance from junction to tie-point	lead length 10 mm	240	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	lead length 10 mm; note 1	350	K/W

Note

1. Device mounted on a printed-circuit board without metallization pad.

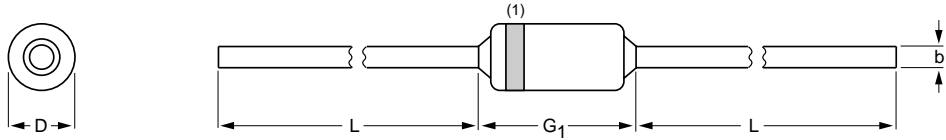
High-speed diodes

1N4148; 1N4448

PACKAGE OUTLINE

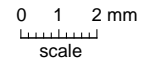
Hermetically sealed glass package; axial leaded; 2 leads

SOD27



DIMENSIONS (mm are the original dimensions)

UNIT	b max.	D max.	G ₁ max.	L min.
mm	0.56	1.85	4.25	25.4



Note

1. The marking band indicates the cathode.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOD27	A24	DO-35	SC-40			97-06-09